

NTE573 Schottky Barrier Rectifier

Description:

The NTE573 is an axial lead metal-to-silicon power diode using the Schottky Barrier principle. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. This device is ideally suited for use in low-voltage, high-frequency inverters, as free wheeling diodes, and polarity protection diodes.

Features:

- Low Forward Voltage
- Low Power Loss
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- High Efficiency
- High Switching Capability

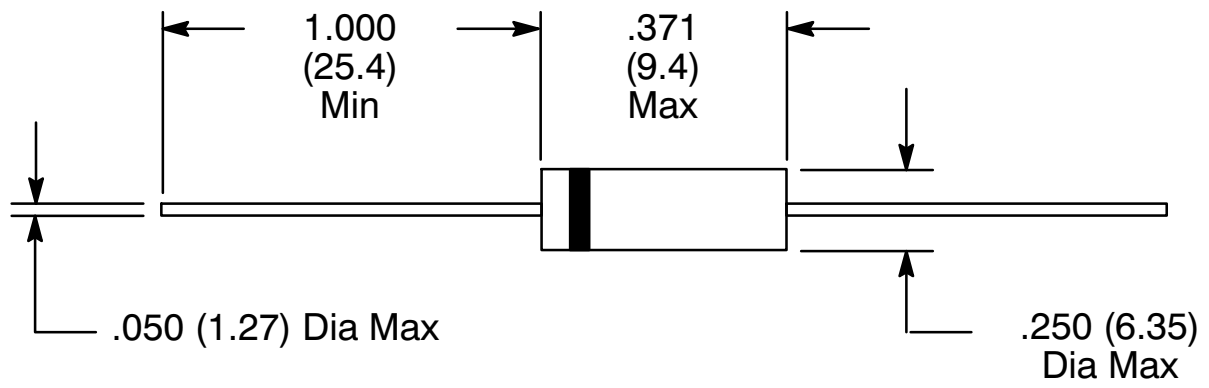
Absolute Maximum Ratings:

Peak Repetitive Reverse Voltage, V_{RRM}	60V
Working Peak Reverse Voltage, V_{RWM}	60V
DC Blocking Voltage, V_R	60V
RMS Reverse Voltage, $V_{R(RMS)}$	42V
Average Forward Rectified Current, I_O	5A
Non-Repetitive Peak Surge Current, I_{FSM} (Surge applied at rated load conditions half-wave, single phase, 60Hz, $T_L = +70^\circ\text{C}$) .	150A
Operating Junction Temperature Range, T_J	-65° to +125°C
Storage Temperature Range, T_{stg}	-65° to +125°C

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Instantaneous Forward Voltage	V_F	$I_F = 5A$	-	-	0.70	V
		$I_F = 15A$	-	-	0.95	V
Instantaneous Reverse Current	I_R	$V_R = 60V, T_L = +25^\circ\text{C}$	-	-	5	mA
		$V_R = 60V, T_L = +100^\circ\text{C}$	-	-	50	mA
Junction Capacitance	C_P	Note 1	-	400	-	pF

Note 1. Measured at 1MHz and applied reverse voltage of 4 volts.



Color Band Denotes Cathode